

Gate Source Voltage	V_{GS}		-4.2		-4.2		-4.2	V	$V_{DS} = 20V, I_D = 50 \mu A$	
		-0.5	-4	-0.5	-4	-0.5	-4	V	$V_{DS} = 20V, I_D = 200 \mu A$	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	-1	-4.5	-1	-4.5	-1	-4.5	V	$V_{DS} = -20V, I_G = 1 nA$	
Gate Source Forward Voltage	$V_{GS(F)}$		2		2		2	V	$V_{DS} = \emptyset V, I_G = 1 mA$	
Drain Saturation Current (Pulsed)	I_{DSS}	0.5	5	0.5	5	0.5	5	mA	$V_{DS} = 20V, V_{GS} = \emptyset V$	

Dynamic Electrical Characteristics

Common Source Forward Transconductance	g_{fs}	1000	3000	1000	3000	1000	3000	μS	$V_{DS} = 20V, V_{GS} = \emptyset V$	f
		1000		1000		1000		μS	$V_{DS} = 20V, V_{GS} = \emptyset V$	f
Common Source Output Capacitance	g_{os}		35		35		35	μS	$V_{DS} = 20V, V_{GS} = \emptyset V$	f
Common Source Input Capacitance	C_{iss}		4		4		4	pF	$V_{DS} = 20V, V_{GS} = \emptyset V$	f
Drain Gate Capacitance	C_{dgo}		1.5		1.5		1.5	pF	$V_{dg} = 10V, I_S = \emptyset A$	f
Common Source Reverse Transfer Capacitance	C_{rss}		1.2		1.2		1.2	pF	$V_{DS} = 20V, V_{GS} = \emptyset V$	f
Noise Figure	NF		0.5		0.5		0.5	dB	$V_{DS} = 20V, V_{GS} = \emptyset V, R_g = 10 M\Omega$	f
Differential Gate Current	$ I_{G1} - I_{G2} $		10		10		10	nA	$V_{DS} = 20V, I_D = 200 \mu A$	T
Saturation Drain Current Ratio	I_{DSS1}/I_{DSS2}	0.95	1	0.95	1	0.95	1		$V_{DS} = 20V, V_{GS} = \emptyset V$	
Differential Gate Source Voltage	$ V_{GS1} - V_{GS2} $		5		10		15	mV	$V_{DS} = 20V, I_D = 200 \mu A$	
Differential Gate Source Voltage with Temperature	$\frac{\Delta V_{GS1} - V_{GS2}}{\Delta T}$		0.8		2		4	mV/°C	$V_{DS} = 20V, I_D = 200 \mu A$	T
			1		2.5		5	mV/°C	$V_{DS} = 20V, I_D = 200 \mu A$	T
Transconductance Ratio	g_{fs1}/g_{fs2}	0.97	1	0.97	1	0.97	1		$V_{DS} = 20V, I_D = 200 \mu A$	f

TO-71 Package

See Section G for Outline Dimensions

Pin Configuration

1 Source, 2 Drain, 3 Gate,
5 Source, 6 Drain, 7 Gate

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